

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1-10 (Cancelled)

Claim 11. (Currently Amended) A method of fabricating a thin film transistor substrate, comprising:

forming a gate electrode on a substrate;

forming a gate insulation layer on the gate electrode and on the substrate;

forming an active layer on the gate insulation layer;

forming source and drain electrodes on the active layer to form a thin film transistor, the source and drain electrodes being spaced apart from each other and located over the gate electrode, wherein the drain electrode has a first side facing the source electrode and a second side facing said first side;

forming a protection layer on the thin film transistor and on the gate insulation layer, wherein forming the protection layer includes etching the protection layer [[covers]] to cover the first side but not the second side of the drain electrode; and

forming a pixel electrode in electrical contact with the second side of the drain electrode, wherein the pixel electrode is formed using a back exposure.

Claim 12. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed overlapping the second side.

Claim 13. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed of a transparent conductive material.

Claim 14. (Original) A method of fabricating a thin film transistor substrate according to claim 13, wherein the transparent conductive material is selected from a group consisting of indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

Claim 15. (Original) A method of fabricating a thin film transistor substrate according to claim 11, wherein the pixel electrode is formed in contact with the gate insulation layer.

Claim 16. (Original) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a gate line on the substrate, wherein the gate line includes a gate pad, and wherein the gate line is formed in electrical contact with the gate electrode;

covering the gate pad with the gate insulation layer and the protection layer;

forming a contact hole through the gate insulation layer and through the protection layer to expose at least part of the gate pad; and

forming a gate pad electrode that electrically contacts the gate pad through the contact hole.

Claim 17. (Original) A method of fabricating a thin film transistor substrate according to claim 16, wherein the gate pad is formed with a bent shape.

Claim 18. (Original) A method of fabricating a thin film transistor substrate according to claim 16, wherein the gate pad electrode is formed on the substrate.

Claim 19. (Original) A method of fabricating a thin film transistor substrate according to claim 11, further including:

forming a data line on the gate insulation layer, wherein the data line includes a data pad, and wherein the data line is formed in electrical contact with the source electrode;

covering the data pad with the protection layer;

forming a contact hole through the protection layer to expose at least part of the data pad; and

forming a data pad electrode that electrically contacts the data pad through the contact hole.

Claim 20. (Original) A method of fabricating a thin film transistor substrate according to claim 19, wherein the data pad is formed with a bent shape.

Claim 21. (Original) A method of fabricating a thin film transistor substrate according to claim 19, wherein the data pad electrode is formed on the gate insulation layer.

Claims 22-31 (Cancelled)